

# Virtual Reliability Qualification

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## **1. Development trends**

## **2. Consequences for reliability**

- Thermo-mechanical problems
- Motivations

## **3. Virtual prototyping and qualification**

- The Methodology
- Status Quo/challenges
- Demonstrators

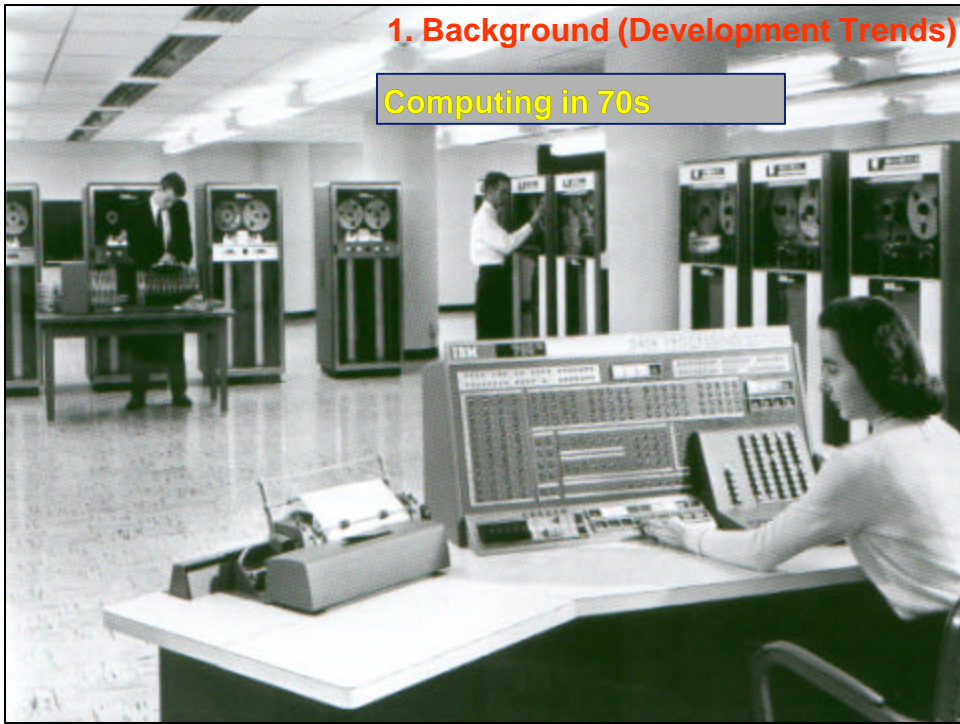
## **4. Conclusions**

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## 1. Development trends

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## 1. Background (Development Trends)

### Consumer Electronics in near future



## Eindhoven University of Technology

- Moving from a world of electronic “boxes” to the world of **ambient intelligence** where technology is built into our environment via connectivity and integration.
- Focus on function, not the devices that enable them.
  - sensitive to people's needs
  - personalized to their requirements
  - anticipatory of their behavior and
  - responsive to their presence

## Consumers wishes

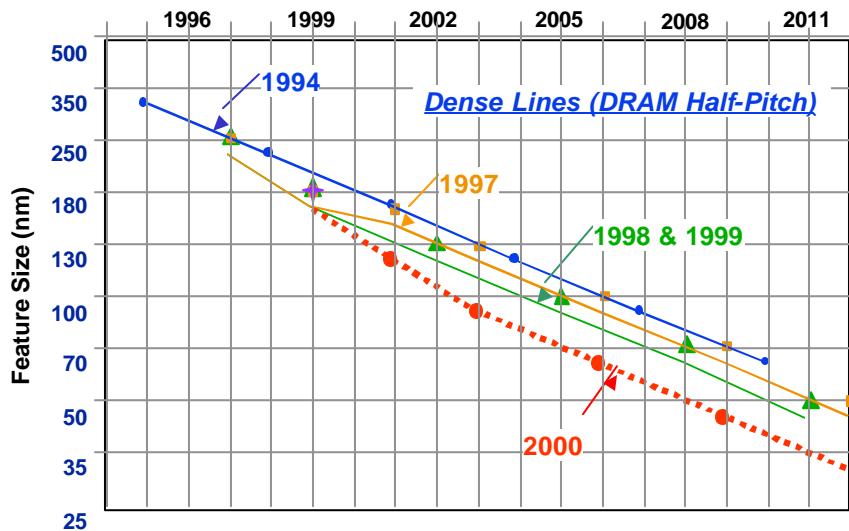
Smaller, smarter, lighter, faster, cheaper, more flexible,  
more convenient, more reliable and functionalities.

## Development trends

- Miniaturisation down to nano-scales
- Increasing levels functionality & technology integration
- Eco-designs
- Cost reduction
- Short-time-to-market
- Outsourcing

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## ITRS Roadmap History



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## Process technology evolution

### *System-on-Chip: standardization*

- Standard CMOS density will continue to grow exponentially, driving down the cost of digital data processing and storage
  - More Moore : **System-on-Chip**
- But realized digital design complexity increasingly lags behind the potential of new technologies, while investments soar
  - Decelerating long-term semiconductor market growth to single digit

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## Is the Roadmap Going to End?

Let's see some famous forecasts

“ I think there is a world market for maybe five computers ”

*Thomas Watson, Chairman of IBM, 1943*

“ Computers in the future may weigh no more than 1.5 tons ”

*Popular Mechanics Magazine, 1949*

“ 640K ought to be enough for anybody ”

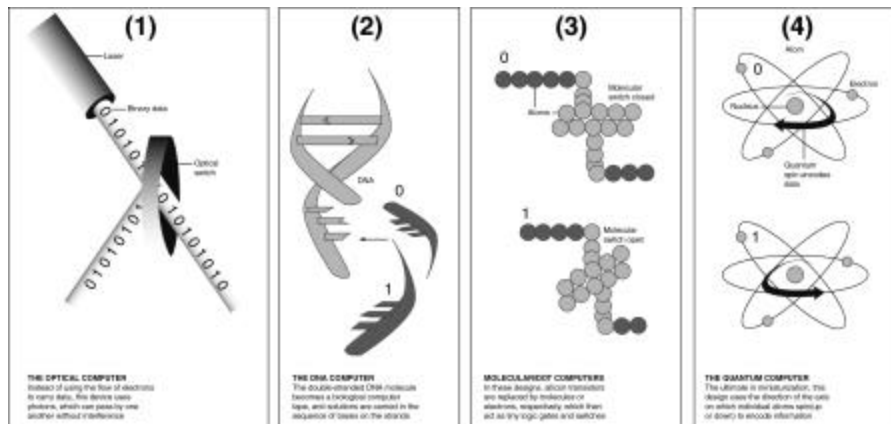
*Bill Gates, 1981*

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## Eindhoven University of Technology

### Alternative Switching Technologies



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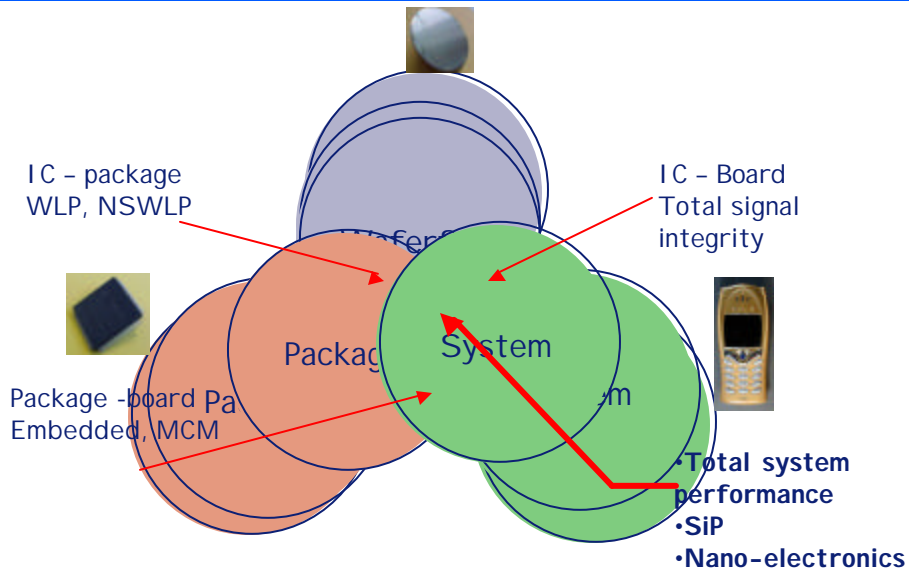
## Eindhoven University of Technology

### Packaging & assembly

- Wire diameter < 10 microns
- Interconnect pitch of NLWSP < 20 microns
- Thickness of copper film/PCB < 10 microns
- Microvia diameter < 20 microns

**Not only the wafer technology, packaging and assembly are also going beyond visualization!**

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## More Moore and more than moore

*Complementing, not competing*

### More Moore: SoC- Programmable monolithic IC

- Advanced baseline CMOS, standard packaging
- Maximize utilization of (expensive) mask sets
- Diversification is in the software & embedded IP mix

### More than Moore: SiP - Multi-technology module

- Mature and advanced wafer processes, advanced packaging
- Maximize utilization of dedicated option fabs
- Diversification is in the components & technology mix



## Examples of technology and function integration

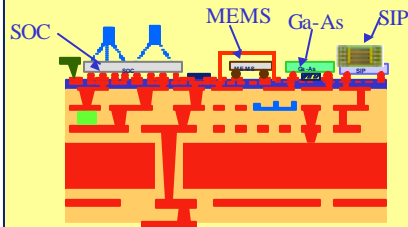
### SIP1

- 3-D Stacking of ICS or Package Structures, Similar to PWB
  - Macro dimensions
  - Vertical stack up
  - Testable
  - System board to Complete



### SIP3

- 3 -D Build up, similar to IC Fabrication
  - Micro to Nano dimensions
  - Sequential build up and test similar to MCM-D and IC
  - Wafer to IC concept for high yield

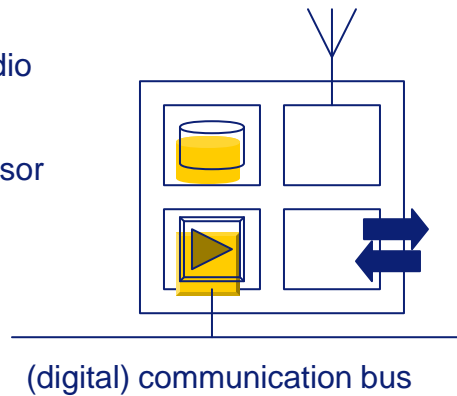


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## Generic sub-system



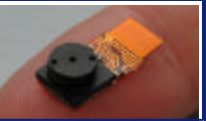
storage radio

$\mu P$  sensor



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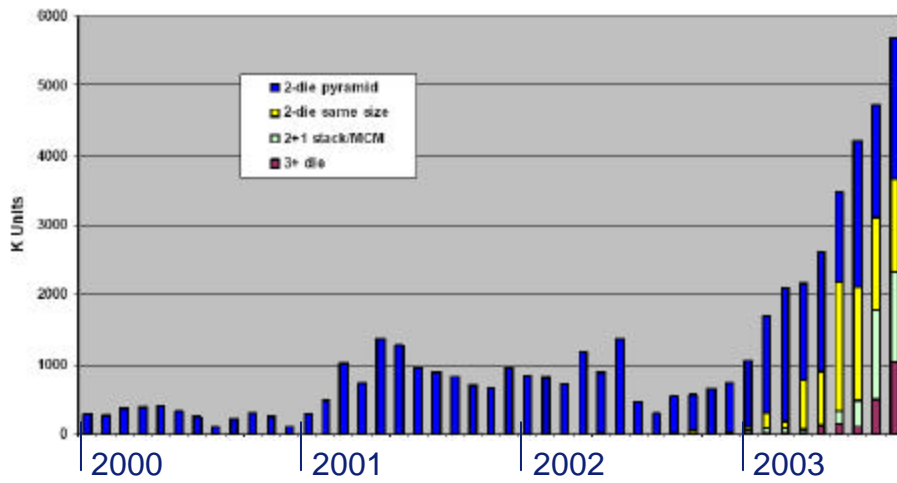
## System-in-Package domains – 3

<i>More than 500</i>	<i>...one IC</i>	<i>...IC process</i>	<i>...electron ics</i>
<b>SiP 1</b> e.g., MCM			
<b>SiP 2</b> e.g., Passive			
<b>SiP 3</b> Integration MOEMS			

® Increasing value proposition

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## Stacked BGA production (leading vendor)



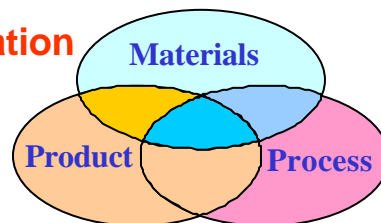
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## Eco-Design

Designing environmentally compatible products/processes while maintaining price/performance and quality characteristics.

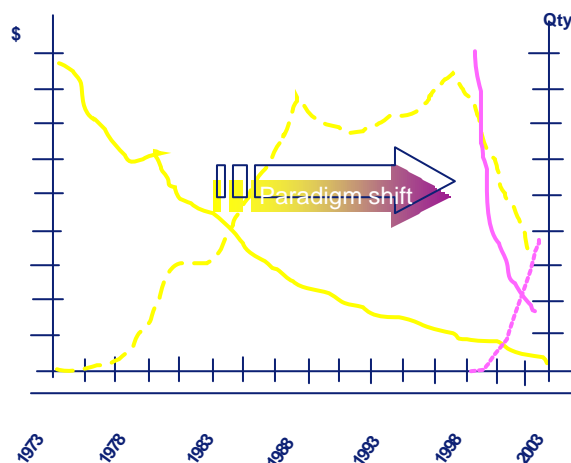
### Key Focus Areas:

- Energy Usage (Products & Manufacturing Processes)
- End-of-Life Management
- Product Packaging
- Removing the boxes
- Virtual prototyping & qualification**



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## Paradigm shift: From Yellow to Purple



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## 2. Consequences for reliability

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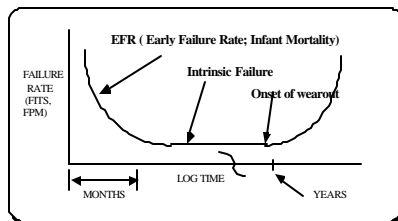
### Reliability

The **probability** that a product in operation will **survive** under certain conditions during a certain period in **time**. IEC50 (191)

### Quality

The **totality** of features and characteristics of a product or service that bear on its ability to **satisfy** stated or implied need. ISO 8420

Conventional  
bathtub curve



**Our scope**  
From 0 hour to life time

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- Multi-scale in both time and geometric domains with scale factors going up to  $10^9$ .

- Strong interactions among different
  - disciplines (electrical, thermal, mechanical, physics, chemical, material science, etc.)
  - technologies (IC, packaging, assembly, system, soft and hardware)
  - failure modes and failure mechanisms

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- Behaviour is strongly non-linear, stochastic, time and temperature dependence.
- Greatly increased loading intensity/loading steps
- Greatly increased design complexity and shrinking of design margin to nano levels.
- Strict demand on and challenges for ensuring quality, robustness and reliability to cover the total value chain

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$$Q\&R = \iiint f_1(b_1, b_2, \dots, b_{i..}) f_2(c_1, c_2, \dots, c_{i..}) f_3(t_1, t_2, \dots, t_{i..}) db dc dt$$

**b:** Business variables

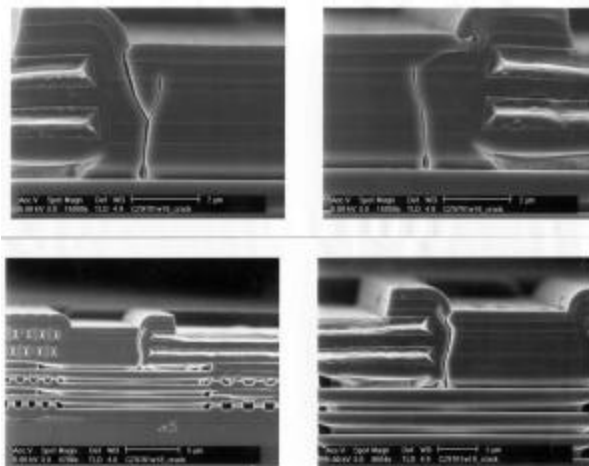
**c:** Consumer variables

**t:** Technical variables

$$f_3(t_1, t_2, \dots, t_{i..}) = \iiint F_1(\text{material}) F_2(\text{process}) F_3(\text{product})$$

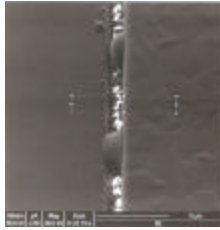
**Q&R is innovation and integration of innovations**

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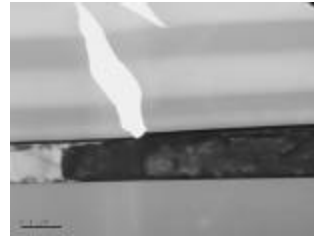
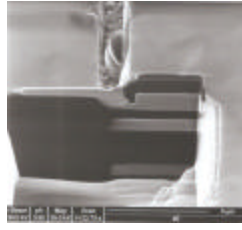


Example of various cracks emanating from the edge of bond pads.  
May be caused by interface defects

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Pattern shift (Power line) caused by packaging stresses



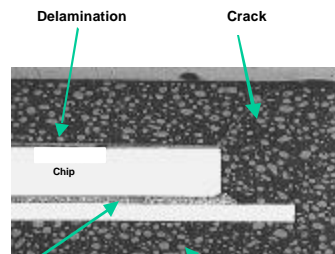
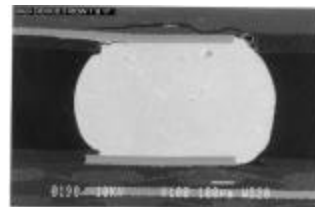
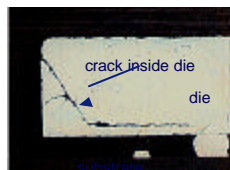
Cracking as a result of electromigration



Warpage caused by wafer thinning:  
200mm wafer thinned to 50  $\mu\text{m}$

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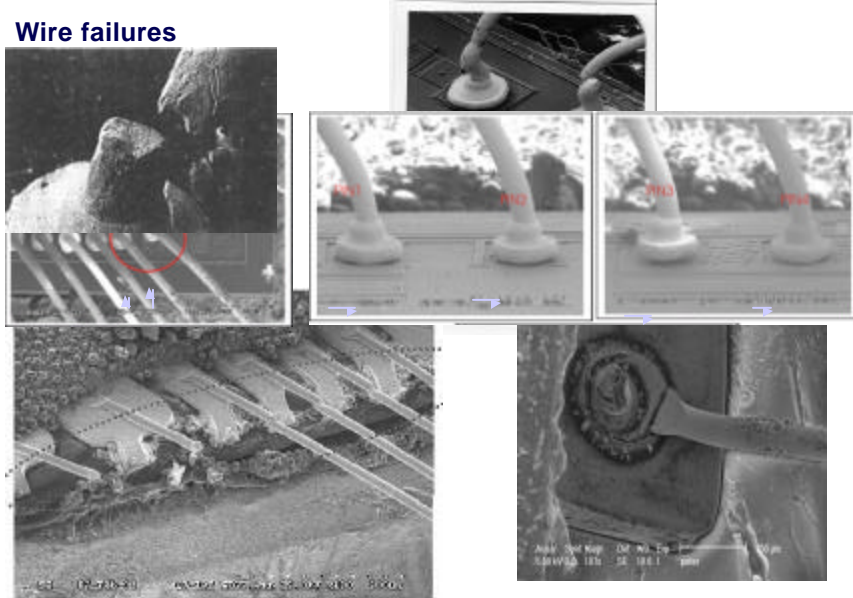
### Die cracking in flip chip



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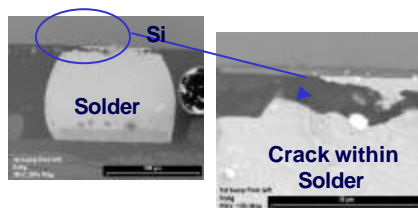


### Wire failures

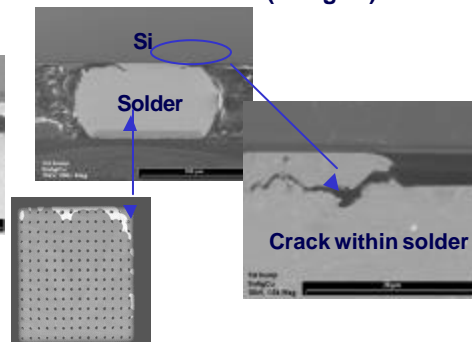


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### Failure Mode (SnAg)

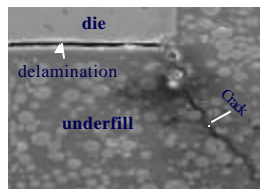
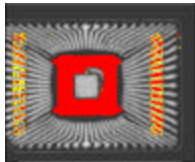
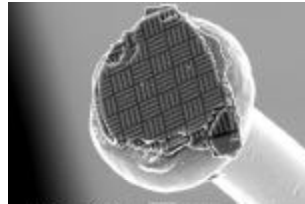
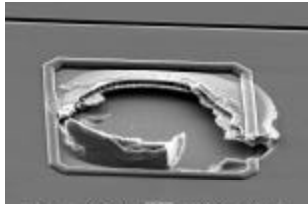


### Failure Mode (SnAgCu)



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## Delamination



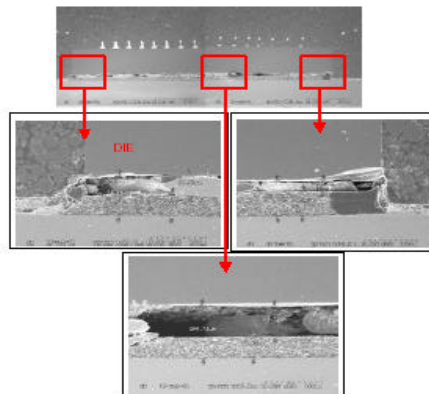
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Chip on Board Globtop Voiding



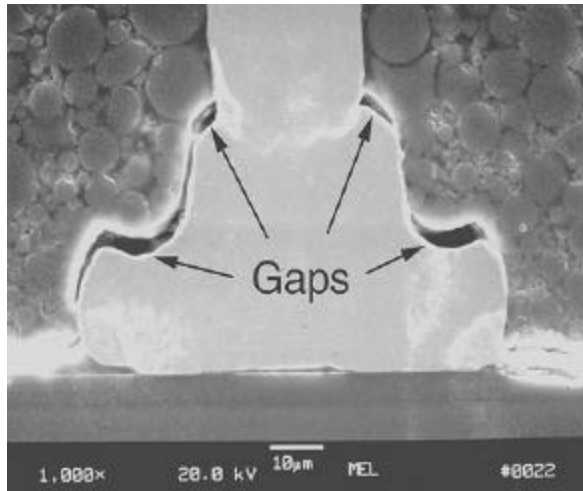
Flip Chip Solder Joint Voiding



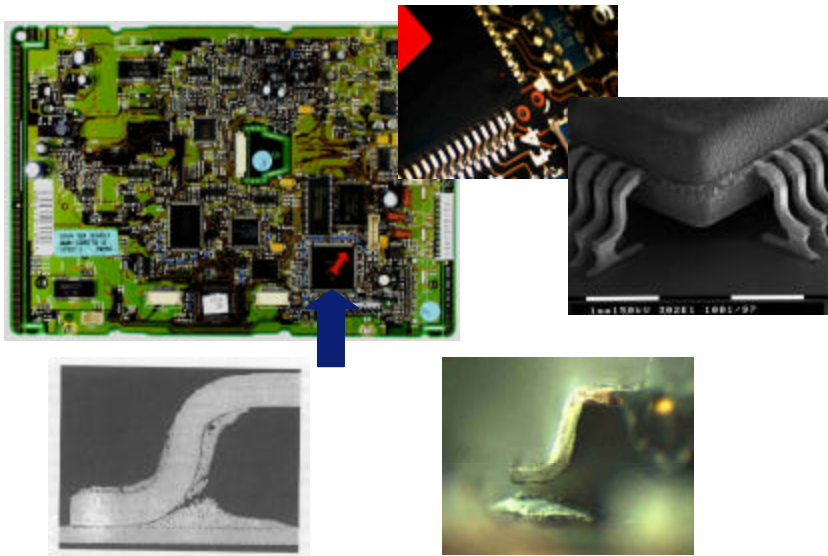
Underfil Voiding

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## Voids caused by molding compound shrinkage



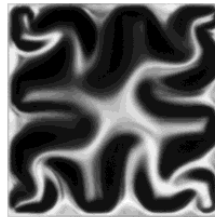
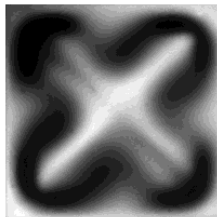
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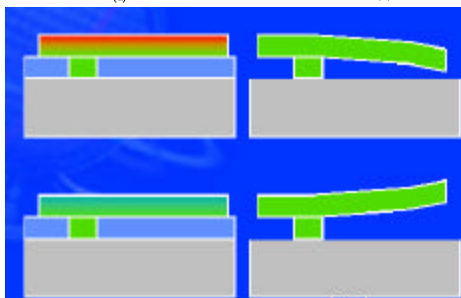


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**MEMS processing challenges:**

**Buckling & postbuckling of membrane during CMOS micromachining**

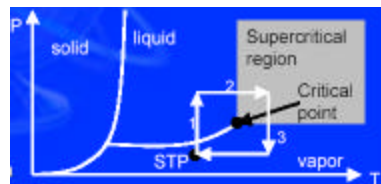
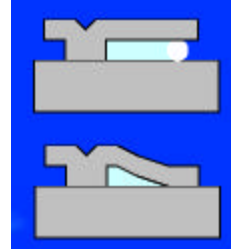


**Stress gradients between the top and the bottom layers of a film**

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## Releasing MEMS: Stiction problem

- Surface forces (van der Waals, hydrogen bonding, etc.) are much stronger than bulk forces (spring restoring forces, gravity)
- Consequence: MEMS stict upon contact
- Common for MEMS that are mechanically compliant or have small gaps



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### Wear out

- Fatigues
- Creep
- Wear
- .....

### Overstress

- Cracks (die, plastic, wirebond, etc. )
- Delamination
- Pop-corn
- Buckling
- Yields (ball shear, pattern shift, etc.)
- Warpage
- Large deformation
- Electro/thermal/stress migration
- Voiding
- .....

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- **New and combined failure modes & mechanisms**
- **>65% of failures thermo-mechanical related!**

**No appropriate thermo-mechanical design method**

- Experience and trial-error based design method
- Empirical, phenomenological, case dependent,
- Sub-optimal product/process
- High development costs

**No appropriate thermo-mechanical qualification method**

- Time and money consuming
- Unclear correlation between application profiles with spec. and accelerated testing
- No guarantee for extrapolating to outside of the spec.
- No satisfied coverage for quality, robustness and reliability

## New Paradigm of Reliability

To meet the needs of tech. trends, a new & knowledge-based Reliability Paradigm is a must.

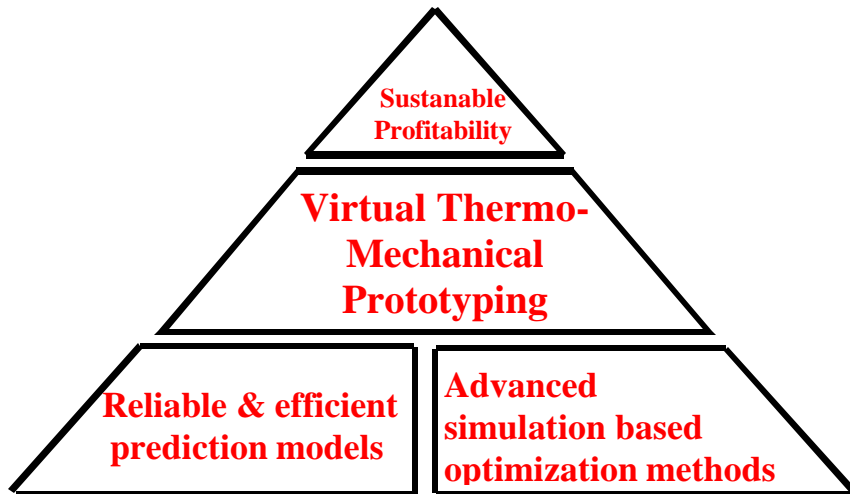
*The scientific successes of many micro/nano-related technology development would never lead to a business success without breakthroughs in the way that we are handling reliability through the whole value chain .*

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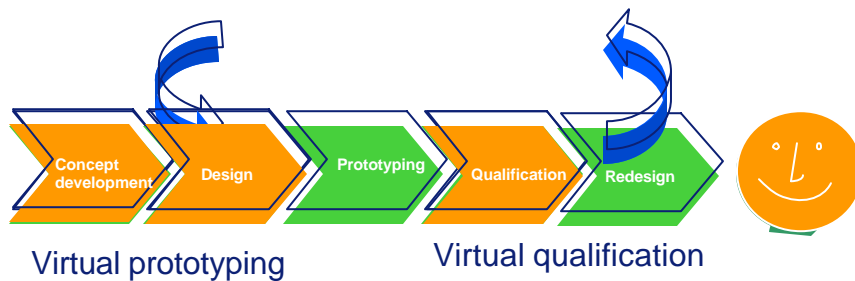
## 3. Virtual prototyping and qualifications

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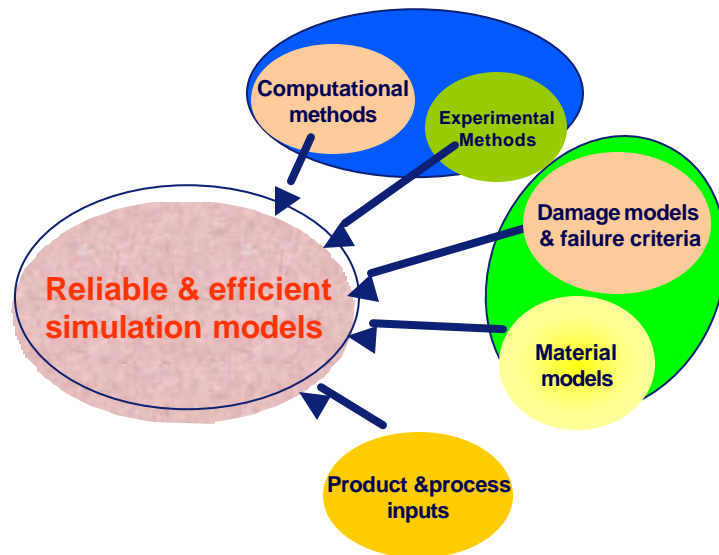
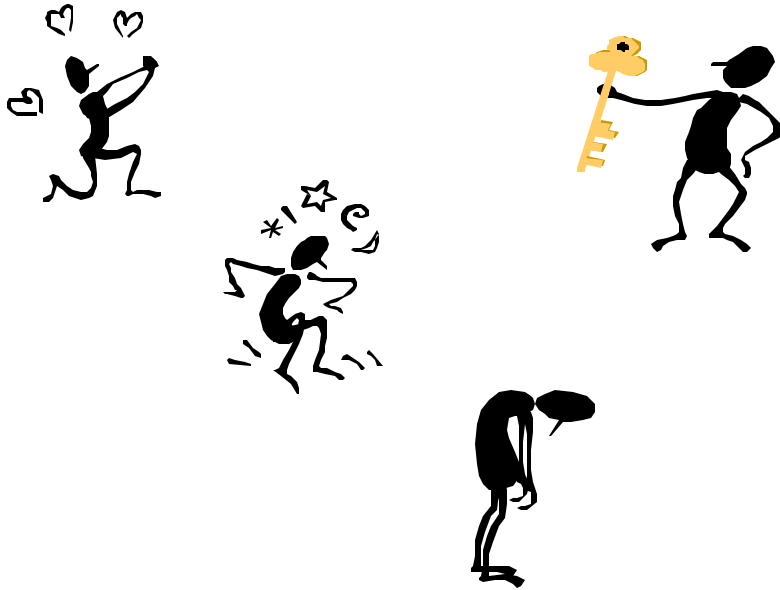
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### Objectives and benefits

- Short-time-to-market
- Cost reduction
- Product/process optimization
- Quality, robustness and reliability insurance

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- Process parameters, reliability qualification

- Product parameters, interface design, etc.

Determining

- loading and loading history; material behavior, initial stress
- damage initiation and evolution



**All statistic in nature**

**!!! Inputs must be reliable**

assembly, testing,

s, tolerance design,



Product & process inputs

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## • Material & damage models

*Laws governing the behavior of materials & interfaces*

- Constitutive law and damage models cannot be partitioned anymore
- Size effects
  - \* Microstructures and their evolutions
  - \* Gradient effect (chemical, electrical, thermal and mechanical)
  - \* Surface effect
- Strong process-dependence
  - Temperature, time, constraint, stress, interfaces & reactions
- Multi-scale damage, initiation, failure criteria and process-dependent evolution
- **Ultimate aim: Material design rules to tailor the properties for specific need**

Damage models & failure criteria

Material models

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Computational  
methods

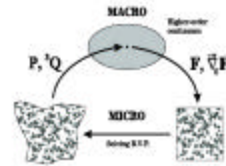
Experimental  
Mechanics

Deterministic

Characterization

Stochastic

- Non-continuum;
- Multi-scale (bridging gaps);
- Multi-physics;
- Multi-failure mode;
- Multi-process;
- Nonlinear;
- 3D applications;
- Efficient & accurate
- **Advanced FEM tool (MARC)**



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In principal, all the simulation results  
are wrong, unless you can prove  
they are right.

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## Simulation based optimization

Optimization based on and integrated with advanced simulation models

- Maximum & minimum
  - Robust design
- Parameter sensitivity

under given bounds of design and response parameters

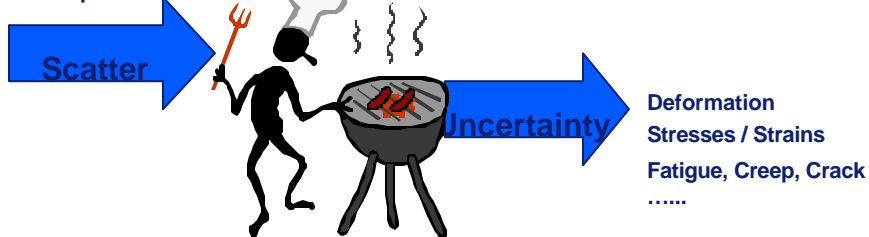
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Material Parameters

Geometry

Boundary Conditions

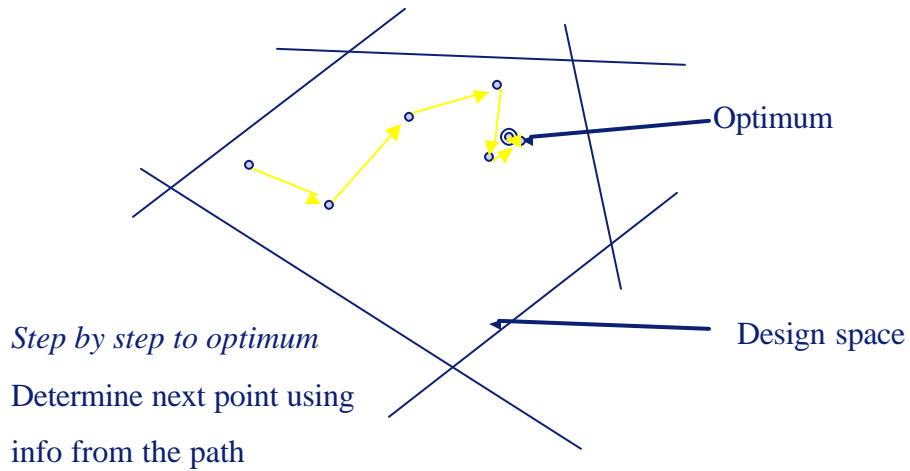
Process parameters



- 1 How large is the scatter of the output parameters?
- 2 What is the probability that output parameters do not fulfil design criteria (failure probability)?
- 3 How much does the scatter of the input parameters contribute to the scatter of the output (sensitivities)?

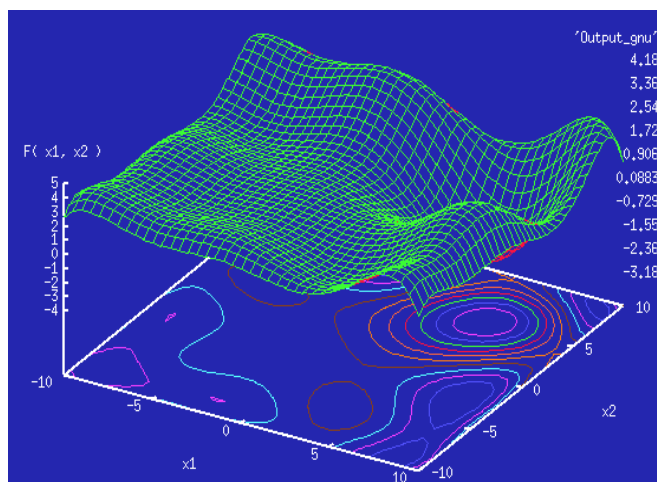
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## Sequential optimization

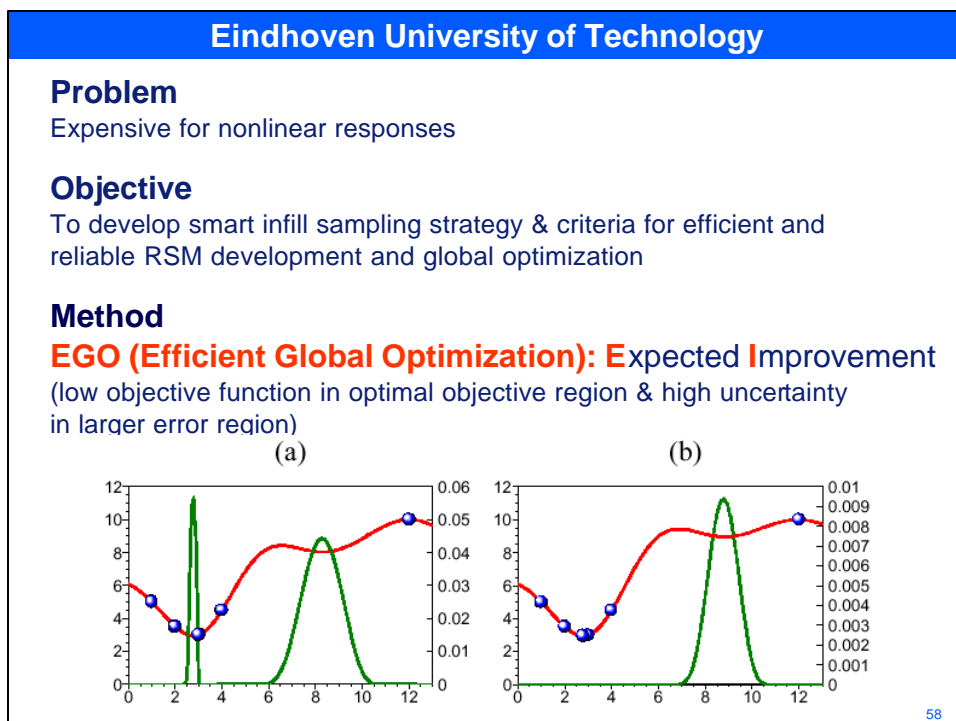
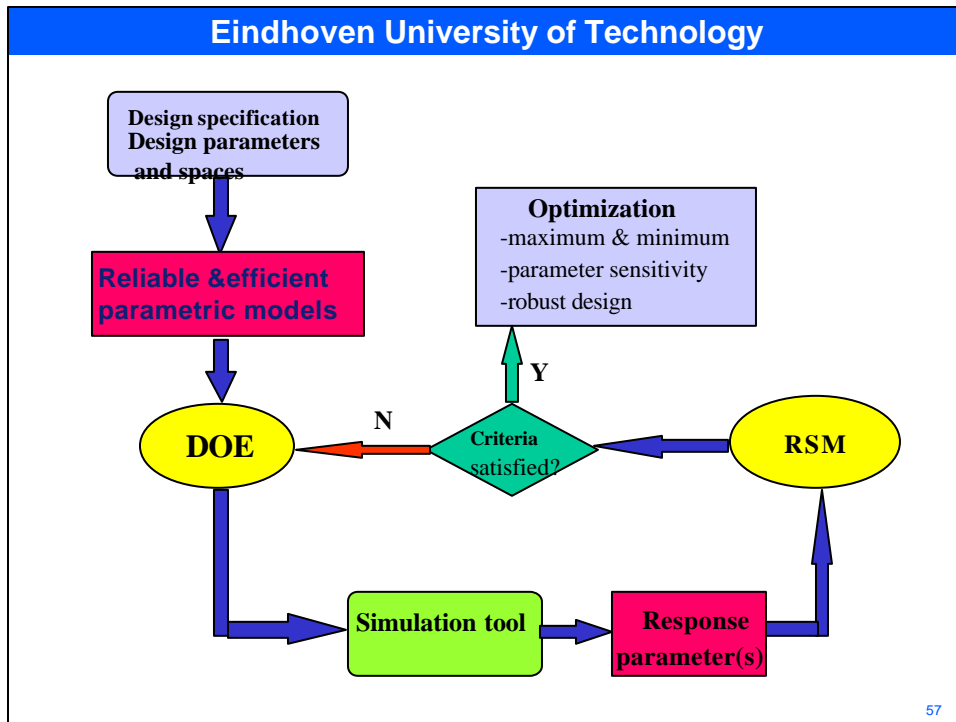


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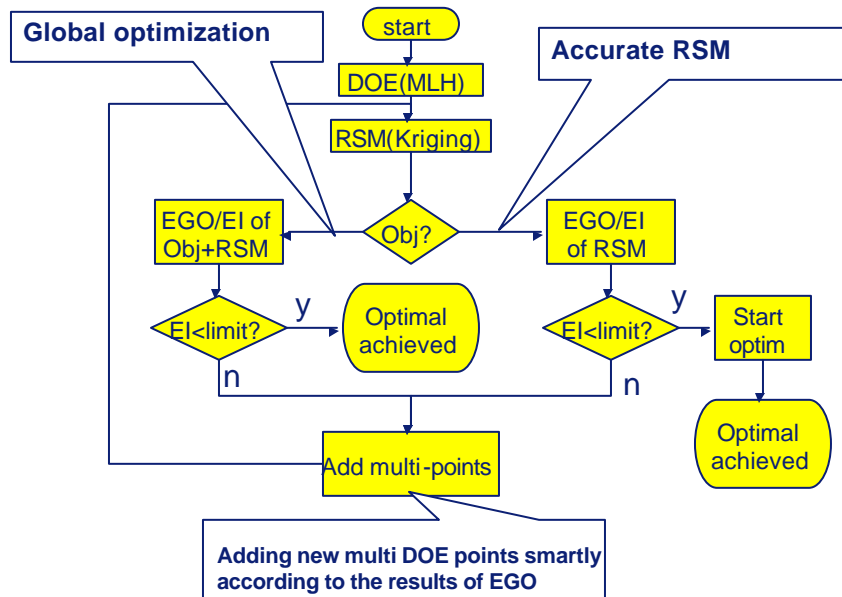
## Compact-model optimization



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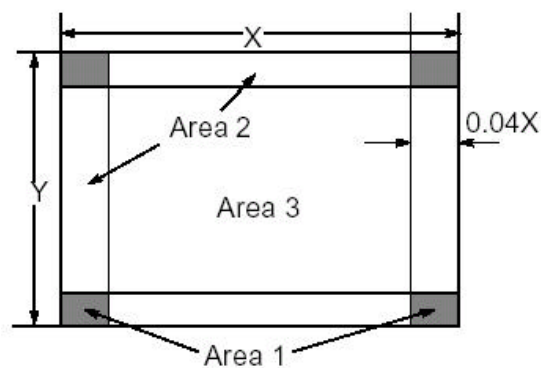




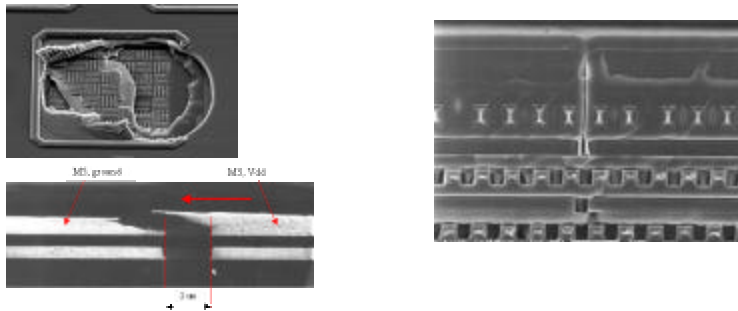
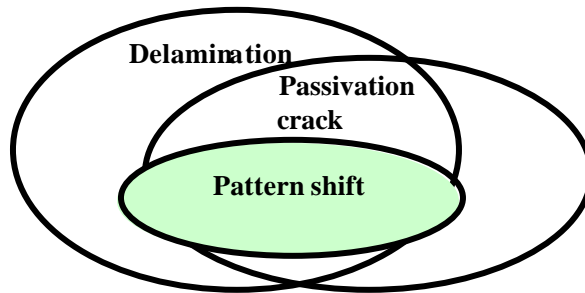


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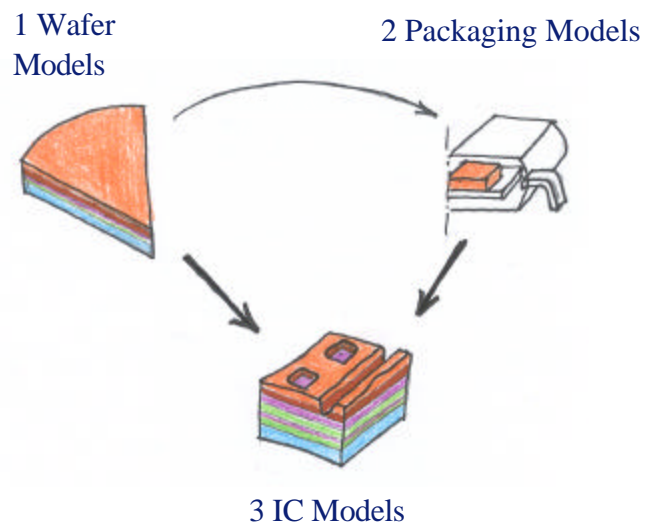
## Current IC stress design rules



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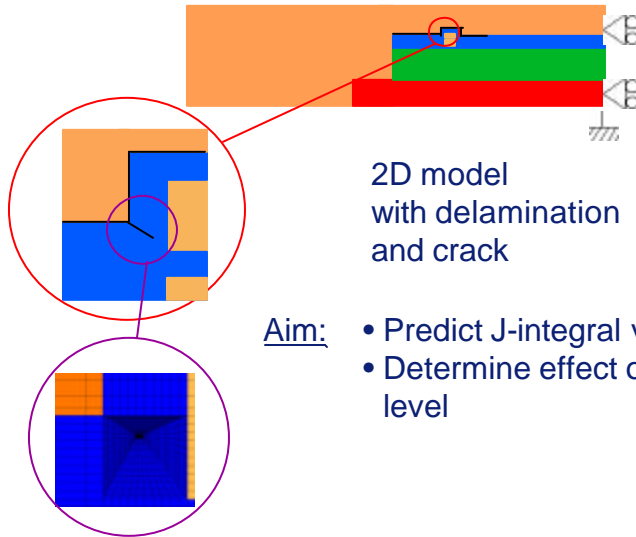


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## Delamination - Crack energy criteria



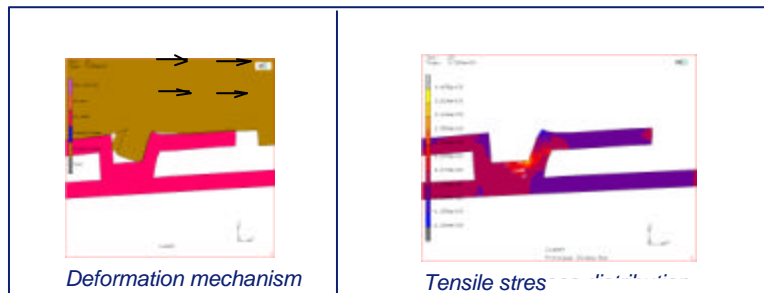
2D model  
with delamination  
and crack

Aim:

- Predict J-integral values
- Determine effect of 2nd metal level

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## Influence of IC/compound delamination on passivation cracks/pattern shift



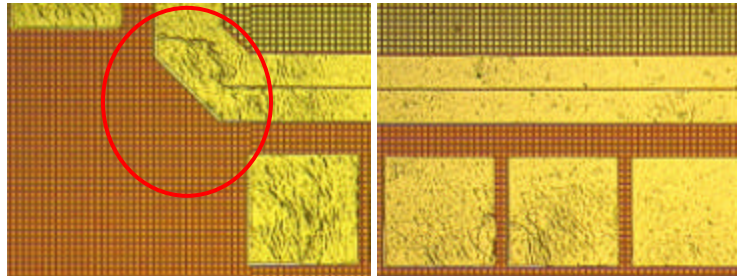
- Delamination may lead to passivation cracks and pattern shift.
- Depending on metal layout.
- Critical crack location is identified.

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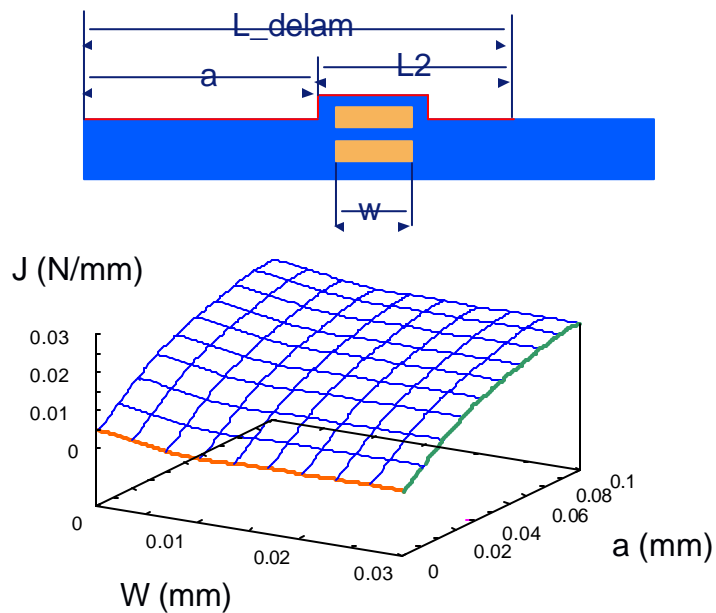
## Experimental and numerical results

- Special test samples designed for the carrier product.
- Observations compared with simulations.
- With the verified models a wide design space simulated.

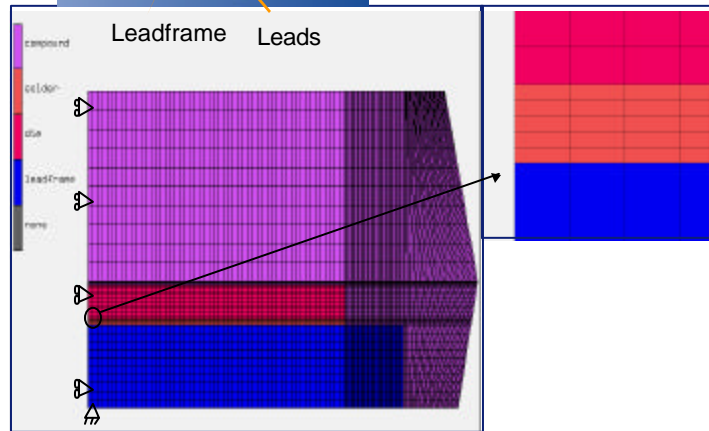
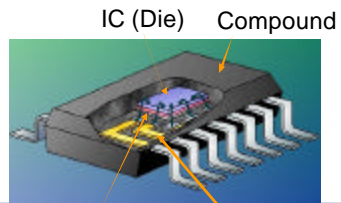
Metal shift



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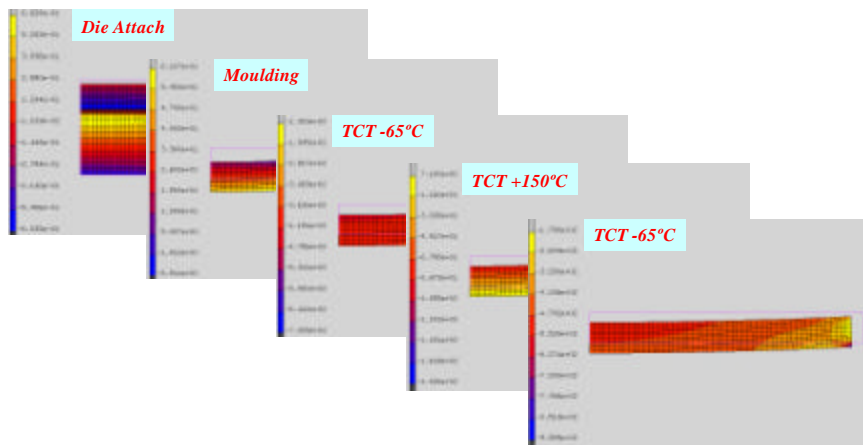


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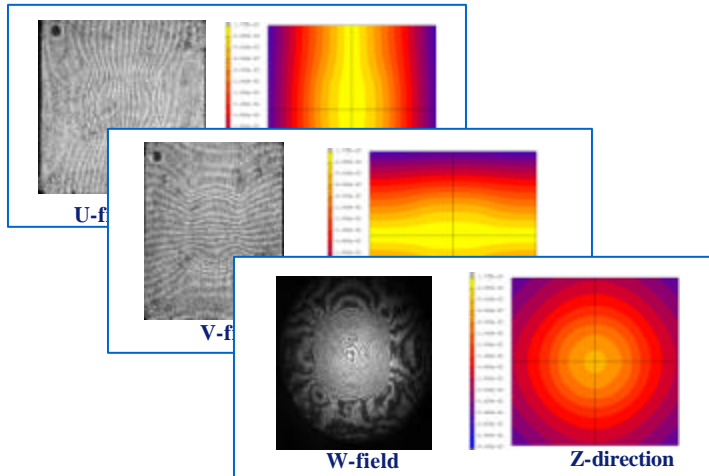
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## Stress Evolution for Nominal Design



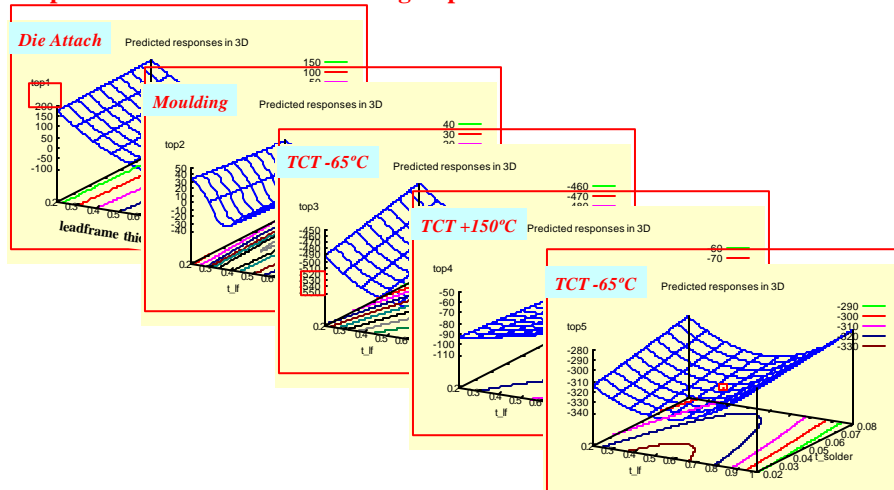
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## Results - Comparison with FEM



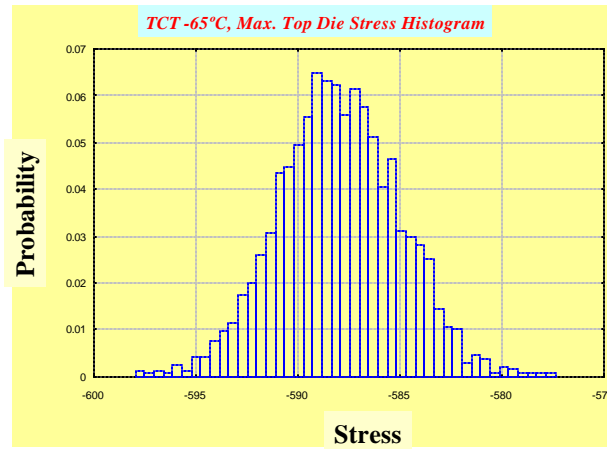
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## Top Die Stress Evolution for Design Space



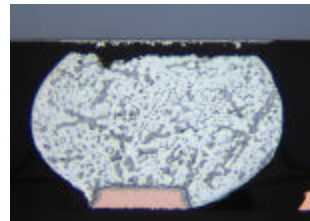
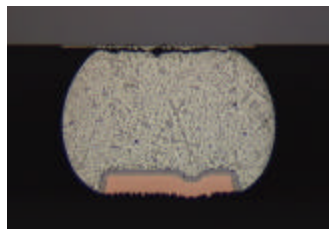
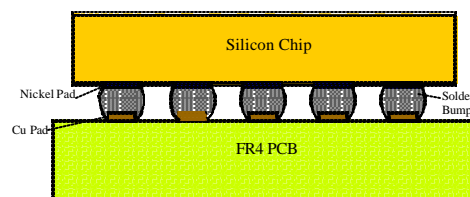
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**Sensitivity to Solder Thickness**



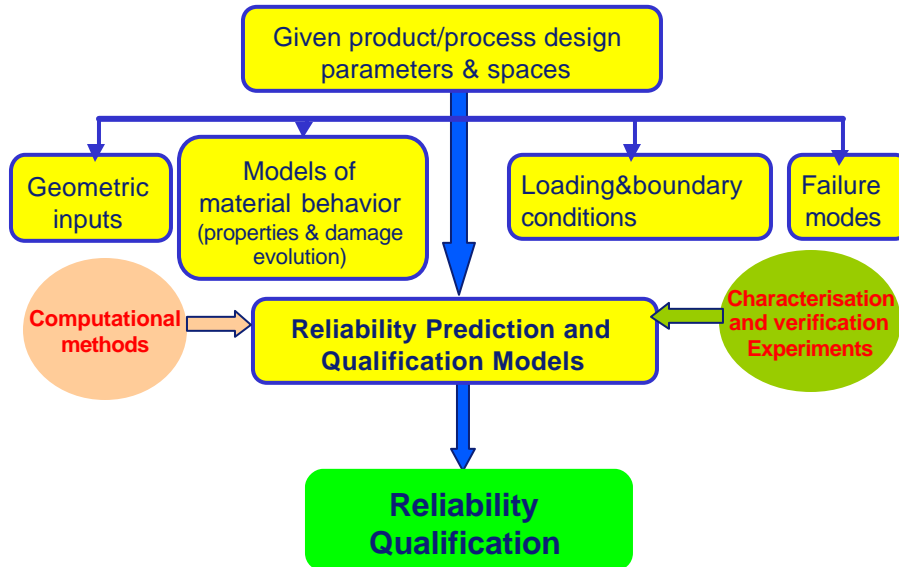
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**Solder joint failure under thermal loading**



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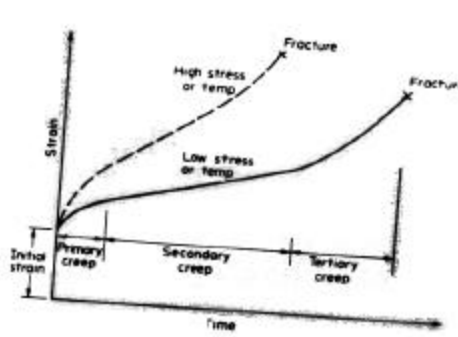
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Homologous temperature (?)

$$T_{\text{hom}} = T_{\text{current}} / T_{\text{melting}}$$

Creep (?)

- Time dependent inelastic strain under constant load and elevated temperature
- Three phases: Primary (decrease SR); secondary constant (SR); tertiary (increase SR)



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$$\dot{\epsilon} = \dot{\epsilon}_{eq}^{el} + \dot{\epsilon}_{eq}^{cr} + \dot{\epsilon}^{pl}$$

$$\dot{\epsilon}^{inel} = \dot{\epsilon}^{cr} + \dot{\epsilon}^{pl} \quad \text{Extended Maxwell}$$

$$\dot{\epsilon}^{inel} = \dot{\epsilon}^{cr} \quad \text{Maxwell}$$

$$\dot{\epsilon}^{inel} = \dot{\epsilon}^{pl} \quad \text{Elastic-plastic}$$

$$\dot{\epsilon}^{inel} = \dot{\epsilon}^{cr} = \dot{\epsilon}^{pl} \quad \text{Bingham}$$

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$$\dot{\epsilon}^{cr} = f_1(\mathbf{s}) f_2(T) f_3(t)$$

$$f_1(\mathbf{s}) = A s^n$$

$$f_1(\mathbf{s}) = B \exp(\alpha s)$$

$$f_1(\mathbf{s}) = C (\exp(\alpha s) - 1)$$

$$f_1(\mathbf{s}) = D \sinh(\beta \alpha)$$

$$f_1(\mathbf{s}) = \{D \sinh(\beta \alpha)\}^m$$

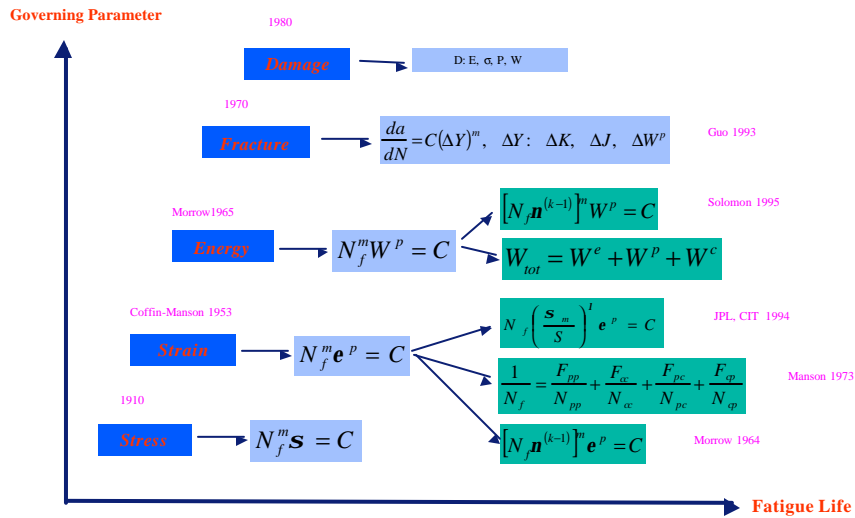
$$f_2(T) = \exp(-Q/RT)$$

R: boltzmann constant; T absolute tem.; Q apparent activation energy

$$f_3(t) = a t^n$$

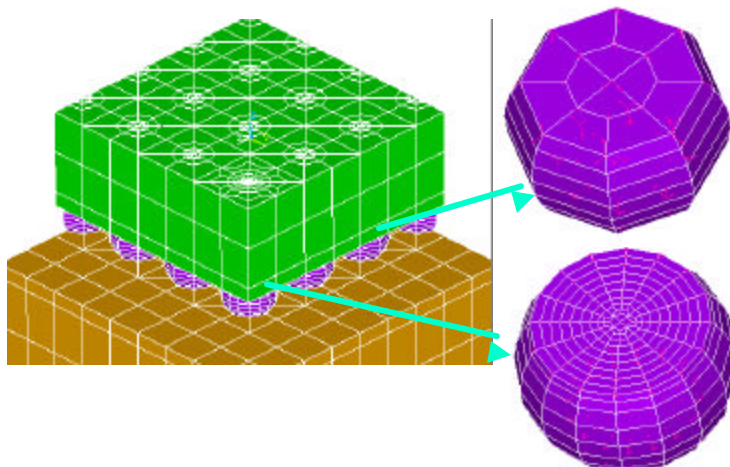
$$f_3(t) = (1 + bt^{1/3}) \exp(kt)$$

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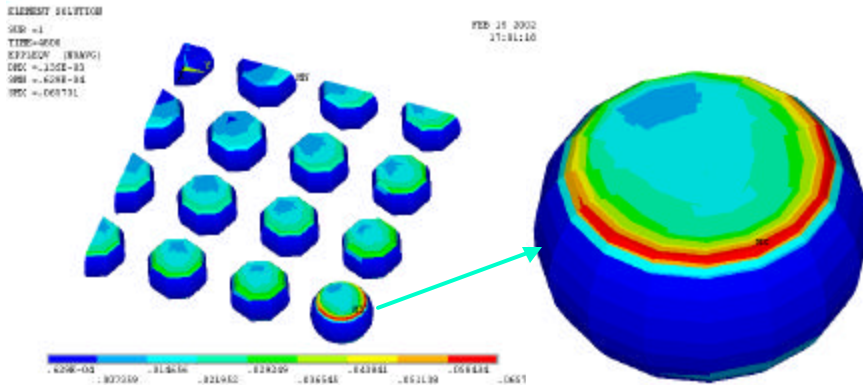
77

## Finite Element Model-7x7Matrix Array



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## Equivalent Plastic Strain Distribution in Solder Joints at the End of 2<sup>nd</sup> Cycle



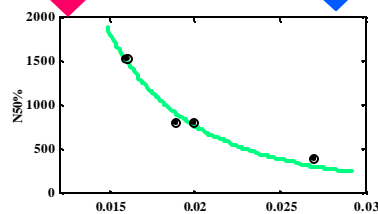
79

## Fatigue Life Model: Manson\_Coffin Based Empirical Model

Cas e	N50% (Test)
A1	1530
A4	711
B2	803
B7	390

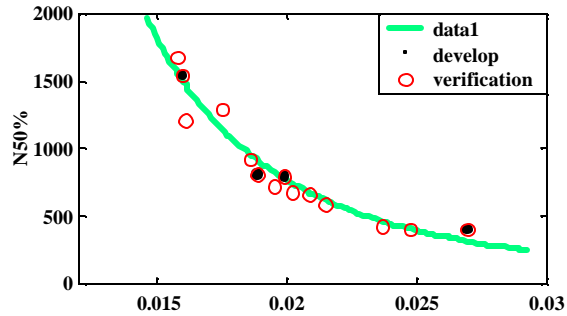
N50%

Strain  
 $De_{av}$



80

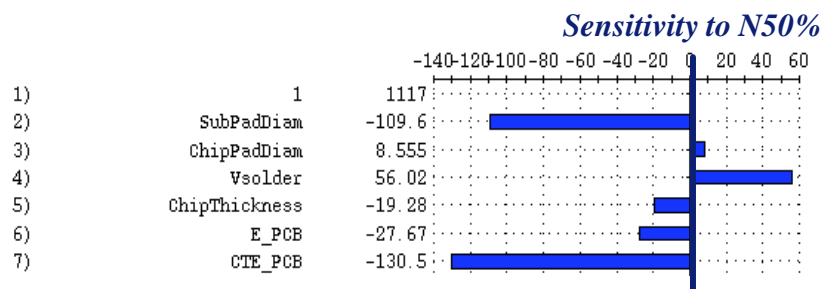
## Fatigue Life Model: Manson\_Coffin Based Empirical Model



$$Life = 0.448(\Delta\epsilon_{10um})^{-2.49}$$

81

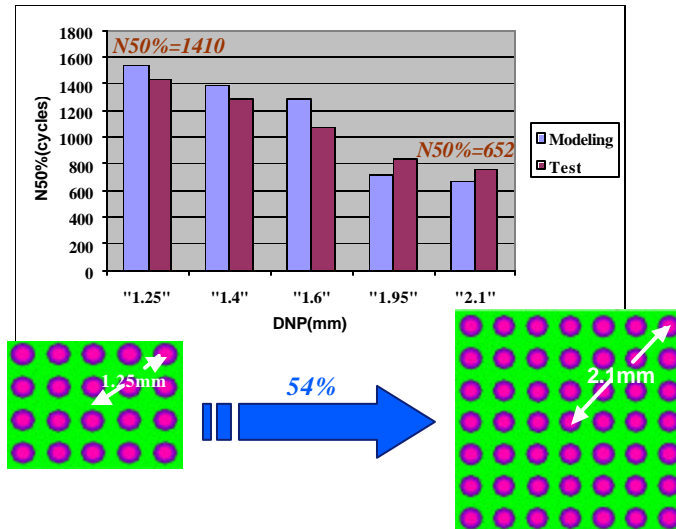
## What are the most sensitive parameters to N50%?



- Most sensitive parameters to N50%:
  - Substrate pad diameter (an increase in substrate value, has a decreasing effect to the reliability N50%)
  - Solder volume
  - CTE of the PCB
- These parameters need a good income inspection

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## Effects of component size (DNP)



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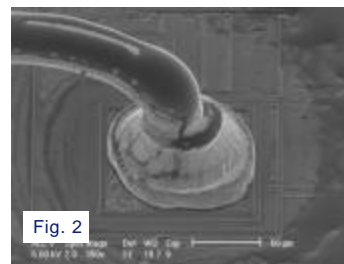
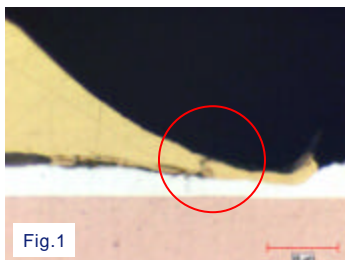
### Example: Optimizing wire loop design to prevent wire break

#### Problem:

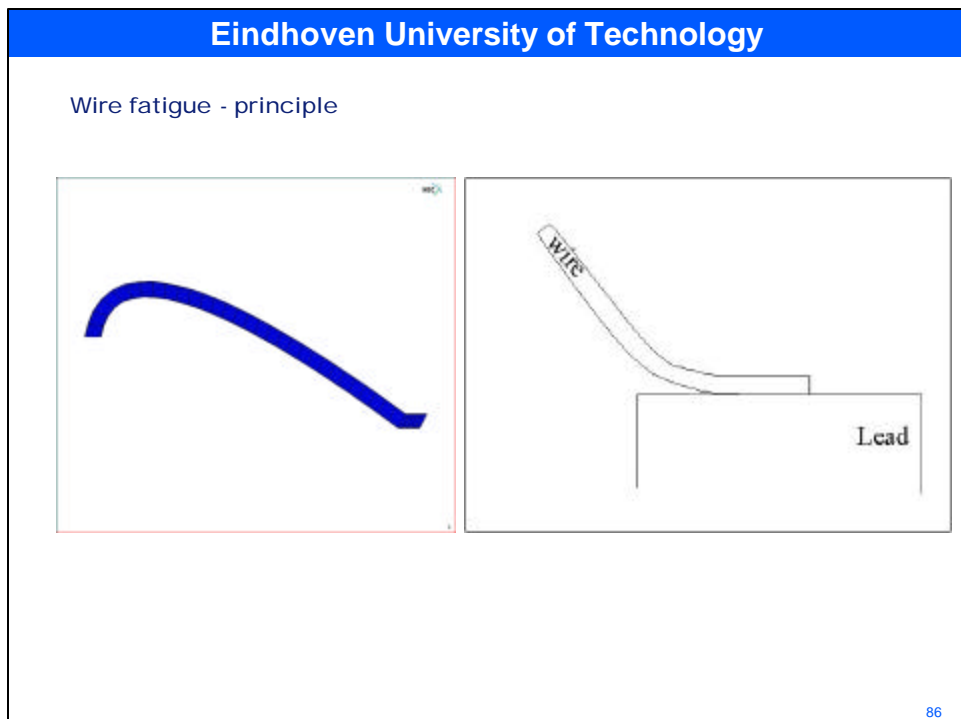
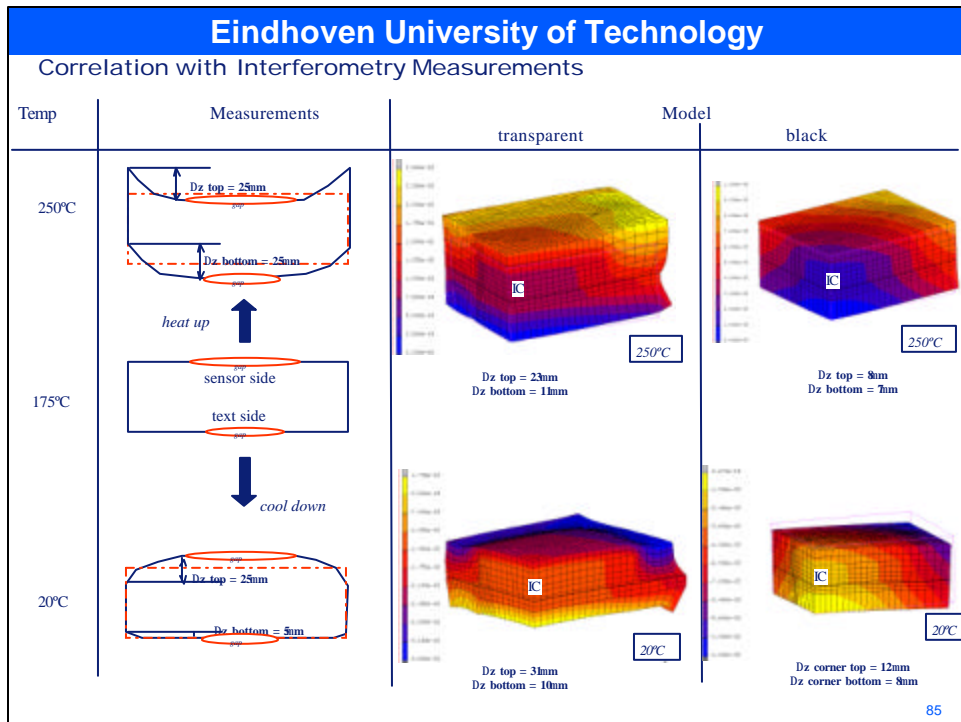
Interconnect wire break is the dominant failure in electronic packaging. Figs. 1 & 2 show the failure on the stitch and the ball side, respectively. There is urgent industrial need to design optimal wire loop in order to prevent possible wire breaks.

#### Method:

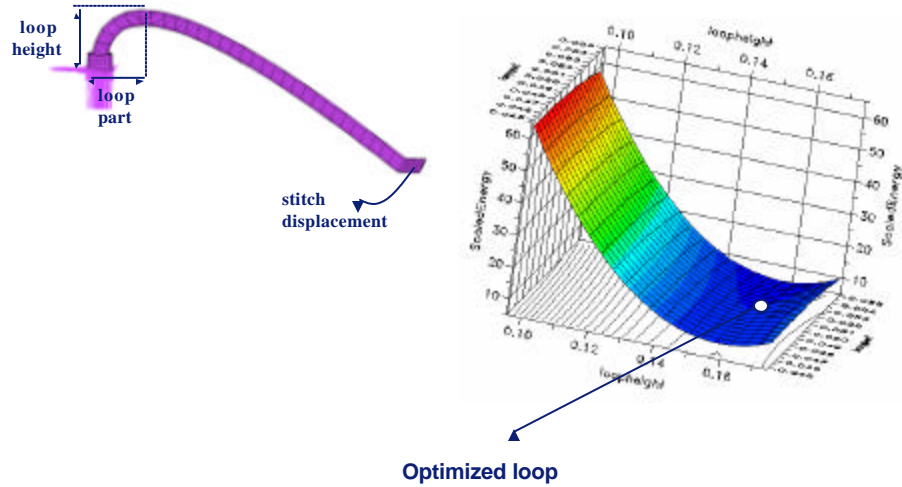
Due to the large scale difference, global-local method is used in developing reliable FEM models to simulate the stress levels in a wire, in combination with nonlinear material model of the wire. From the global package model, wire deformations are obtained and serve as the input for the local wire model.



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Result: Optimized wire shape



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## 4. Conclusions

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- Future technology/business development trends demand virtual prototyping/virtual qualifications.
- The developed methodologies can generate high added business values.
- Not to replay physical prototyping/qualification, but to reduce their numbers and duration.
- Many challenges remain. Combined effort needed.